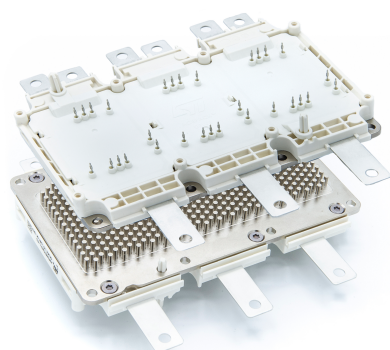
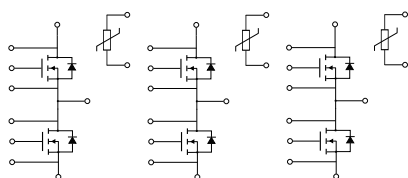


Automotive-grade ACEPACK DRIVE power module, sixpack topology 750 V, 1.2 mΩ typ. SiC MOSFET gen.3 based



ACEPACK DRIVE



Features

- AQC 324 qualified 
- 750 V blocking voltage
- 1.2 mΩ of typical $R_{DS(on)}$
- Maximum operative junction temperature $T_J = 175\text{ °C}$
- Very low switching energy
- Low inductive compact design for an higher power density
- Si_3N_4 AMB substrate to improve thermal performance
- SiC Power MOSFET chip sintered to substrate for improved lifetime
- 4.2 kV DC 1 s insulation
- Directly liquid cooled base plate with pin-fins
- Three integrated NTC temperature sensors
- Long AC bus bar compatible with phase current sense

Application

- Main inverter (electric traction)

Description

The ACEPACK DRIVE is a compact sixpack module optimized for hybrid and electric vehicles traction inverter. This power module features switches based on silicon carbide Power MOSFET 3rd generation, are characterized by very low $R_{DS(on)}$, very limited switching losses and outstanding performances in synchronous rectification working mode. This will ensure superb efficiency in final application, saving battery recharging cycles.

A copper base plate with pin-fin base structure make direct fluid cooling available for this power module minimizing thermal resistance.

A dedicated pin-out has been developed to get the best switching performances and press-fit pins will ensure optimal connection with driving board.



Product status link

[ADP61075W3-L](#)

Product summary

Order code	ADP61075W3-L
Marking	ADP61075W3-L
Package	ACEPACK DRIVE
Leads type	Press-fit
Packing	Tray

1 Electrical ratings

Table 1. Absolute maximum ratings of each switch

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	750	V
V_{GS}	Gate-source voltage	-10 to 22	V
	Gate-source voltage (recommended operating values)	-5 to 18	
I_D	Continuous drain current at $T_F = 75\text{ °C}$ (refer to $T_J \text{ max} = 175\text{ °C}$, $V_{GS} = 18\text{ V}$)	623	A
$I_{DM}^{(1)}$	Repetitive peak drain current	1300	A
P_{TOT}	Total power dissipation at $T_F = 75\text{ °C}$ (refer to $T_J \text{ max} = 175\text{ °C}$, $V_{GS} = 18\text{ V}$)	869	W
T_J	Operating junction temperature range under switching conditions	-40 to 175 ⁽²⁾	°C

1. Pulse width limited by maximum junction temperature.
2. Maximum baseplate temperature has to be always limited to 125 °C.

Table 2. Thermal data of each switch

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{thJF}^{(1)}$	Thermal resistance, junction-to-fluid (flow rate = 10 LPM, $T_F = 75\text{ °C}$, single switch)	-	0.105	-	°C/W

1. Simulated value considering 50% water/ 50% ethylene glycol cooling fluid. Refer to TN1412 "ACEPACK DRIVE assembly instructions" for water jacket design.

2 Electrical characteristics

$T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise specified.

Table 3. Electrical characteristics of each switch

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$R_{DS(on)}^{(1)}$	Static drain-source on-resistance	$V_{GS} = 18\text{ V}, I_D = 610\text{ A}$		1.20	1.60	m Ω
		$V_{GS} = 18\text{ V}, I_D = 610\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$		1.95		
		$V_{GS} = 18\text{ V}, I_D = -610\text{ A}$		1.15		
		$V_{GS} = 18\text{ V}, I_D = -610\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$		1.85		
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 50\text{ mA}$	1.9	3.1	4.4	V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}, V_{DS} = 750\text{ V}$			100	μA
		$V_{GS} = 0\text{ V}, V_{DS} = 750\text{ V}, T_J = 150\text{ }^{\circ}\text{C}^{(2)}$			2	mA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}, V_{GS} = -10\text{ to }22\text{ V}$			± 2	μA
C_{iss}	Input capacitance	$V_{DS} = 400\text{ V}, f = 1\text{ MHz}, V_{GS} = 0\text{ V}$		36.07		nF
C_{oss}	Output capacitance			2.85		nF
C_{rss}	Reverse transfer capacitance			0.21		nF
Q_g	Total gate charge	$V_{DS} = 400\text{ V}, I_D = 610\text{ A},$ $V_{GS} = -5\text{ V to }18\text{ V}$		1312		nC
Q_{gs}	Gate-source charge			430		nC
Q_{gd}	Gate-drain charge			368		nC

- $R_{DS(on)}$ is referred to switch level.
- Specified by design, not tested in production.

Table 4. Switching energy of each switch

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$	Turn-on switching energy	$V_{DD} = 400\text{ V}, V_{GS} = -5\text{ to }18\text{ V},$ $R_{G(on)} = 15\text{ }\Omega, di/dt_{on} = 3.0\text{ A/ns},$ $I_D = 610\text{ A}$	-	36.8	-	mJ
		$V_{DD} = 400\text{ V}, V_{GS} = -5\text{ to }18\text{ V},$ $R_{G(on)} = 15\text{ }\Omega, di/dt_{on} = 3.8\text{ A/ns},$ $I_D = 610\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$	-	24.6	-	
E_{off}	Turn-off switching energy	$V_{DD} = 400\text{ V}, V_{GS} = -5\text{ to }18\text{ V},$ $R_{G(off)} = 8.2\text{ }\Omega, dV/dt_{off} = 3.2\text{ V/ns},$ $I_D = 610\text{ A}$	-	32.6	-	mJ
		$V_{DD} = 400\text{ V}, V_{GS} = -5\text{ to }18\text{ V},$ $R_{G(off)} = 8.2\text{ }\Omega, dV/dt_{off} = 3.8\text{ V/ns},$ $I_D = 610\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$	-	28.5	-	

- Using active Miller clamp circuit.

Table 5. Source-drain diode characteristics of each switch

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{SD}	Forward on voltage drop	$V_{GS} = -5\text{ V}$, $I_D = 610\text{ A}$	-	4.3	-	V
t_{rr}	Reverse recovery time	$V_{DD} = 400\text{ V}$, $V_{GS} = -5\text{ V to } 18\text{ V}$, $R_{G(on)} = 15\text{ }\Omega$, $di/dt_{on} = 3.0\text{ A/ns}$, $I_D = 610\text{ A}$	-	42	-	ns
Q_{rr}	Reverse recovery charge		-	2.6	-	μC
I_{RRM}	Reverse recovery current		-	110	-	A
E_{rec}	Reverse recovery energy		-	0.47	-	mJ
t_{rr}	Reverse recovery time	$V_{DD} = 400\text{ V}$, $V_{GS} = -5\text{ V to } 18\text{ V}$, $R_{G(on)} = 15\text{ }\Omega$, $di/dt_{on} = 3.8\text{ A/ns}$, $I_D = 610\text{ A}$, $T_J = 175\text{ }^\circ\text{C}$	-	50	-	ns
Q_{rr}	Reverse recovery charge		-	4.8	-	μC
I_{RRM}	Reverse recovery current		-	168	-	A
E_{rec}	Reverse recovery energy		-	1.1	-	mJ

Note: Values are calculated taking in account an active Miller clamp circuit.

3 NTC

Table 6. Absolute maximum ratings for NTC temperature sensor, considered as standalone

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
R ₂₅	Rated resistance	T = 25 °C		5.0		kΩ
R ₁₀₀	Rated resistance	T = 100 °C		493		Ω
ΔR/R	Deviation of R ₁₀₀		-5		+5	%
B _{25/50}	B-constant			3375		K
B _{25/80}				3411		K

4 ACEPACK DRIVE power module details

Table 7. Ratings for module

Symbol	Parameter		Value	Unit
V_{ISO}	Isolation voltage (f = 0 Hz, t = 1 s)		4.2	kV
	Internal isolation (class 1, IEC 61140)		Si ₃ N ₄	
	Baseplate module material		Ni plated, Cu baseplate	
d_{creep}	Creepage distance	Terminal to heat sink	9.0	mm
		Terminal to terminal	9.0	
d_{clear}	Clearance distance	Terminal to heat sink	4.5	mm
		Terminal to terminal	4.5	
CTI	Comparative tracking index		>200	V
L_s	Typical stray inductance drain to source module loop		10	nH
R_s	Typical module lead resistance, terminals to chip		0.5	mΩ
T_{stg}	Storage temperature range		-40 to 125	°C

5 Electrical characteristics (curves)

Figure 1. Typical output characteristics ($T_J = -40\text{ }^{\circ}\text{C}$)

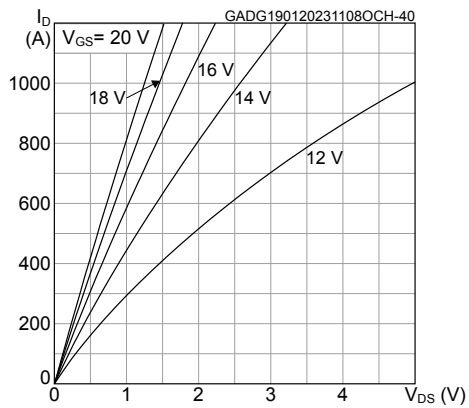


Figure 2. Typical output characteristics ($T_J = 25\text{ }^{\circ}\text{C}$)

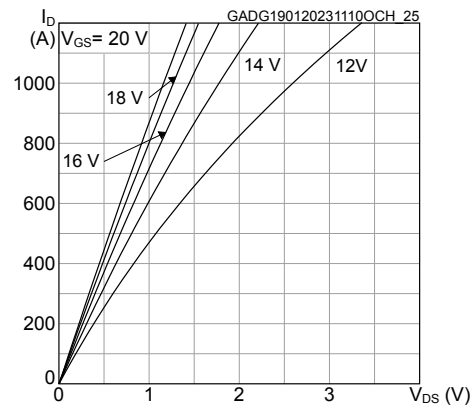


Figure 3. Typical output characteristics ($T_J = 175\text{ }^{\circ}\text{C}$)

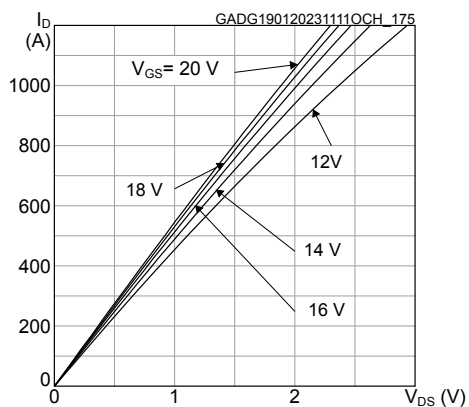


Figure 4. Typical reverse conduction characteristics ($T_J = -40\text{ }^{\circ}\text{C}$)

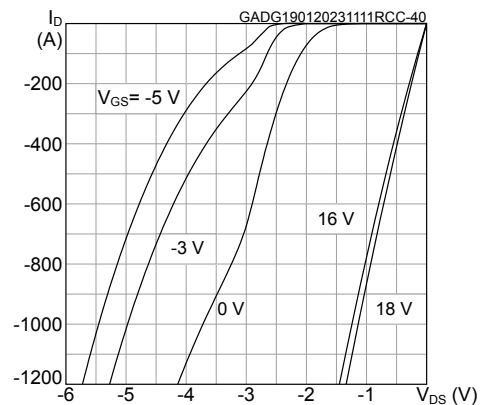


Figure 5. Typical reverse conduction characteristics ($T_J = 25\text{ }^{\circ}\text{C}$)

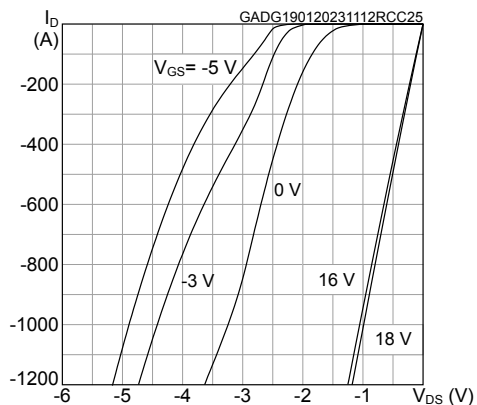


Figure 6. Typical reverse conduction characteristics ($T_J = 175\text{ }^{\circ}\text{C}$)

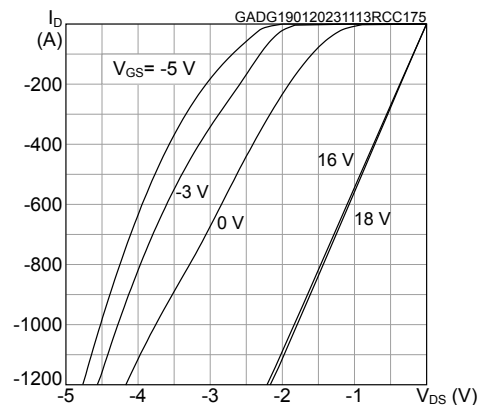


Figure 7. Typical transfer characteristics

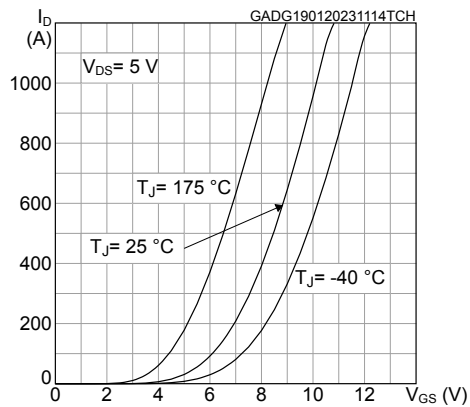


Figure 8. Normalized breakdown voltage vs temperature



Figure 9. Typical switching energy vs drain current

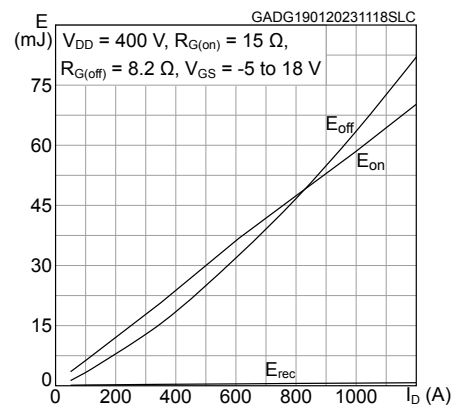


Figure 10. Typical switching energy vs gate resistance

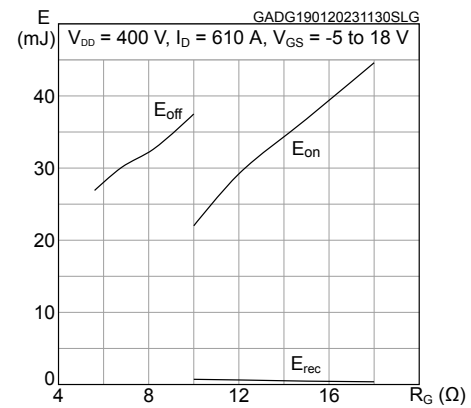


Figure 11. Typical switching energy vs temperature

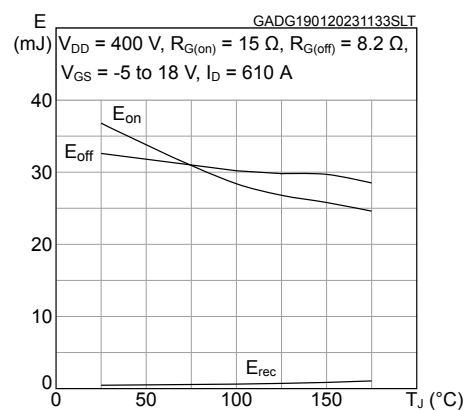


Figure 12. Typical switching energy vs bus voltage

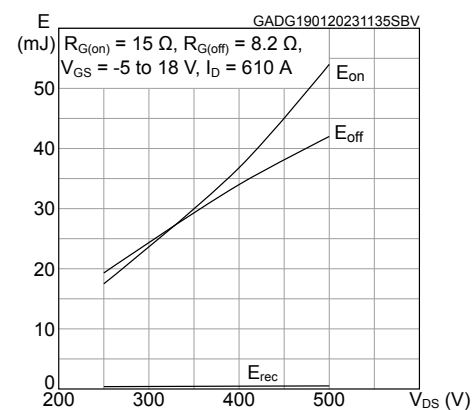


Figure 13. Typical capacitance characteristics

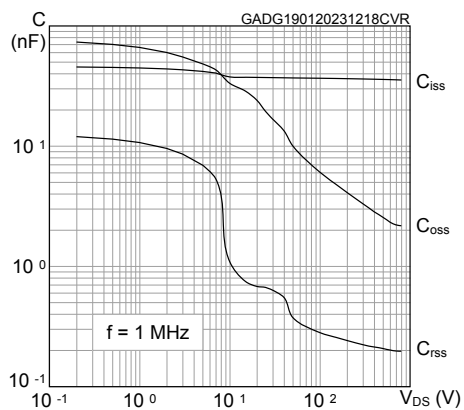


Figure 14. Typical gate charge characteristics

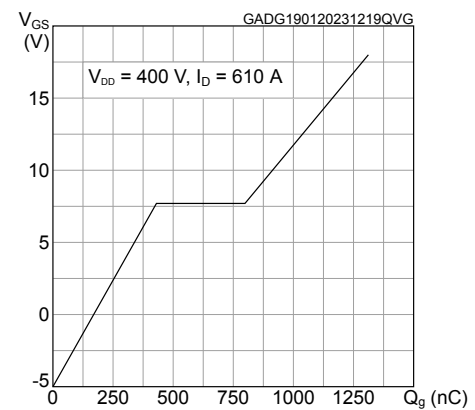


Figure 15. Typical transient thermal impedance

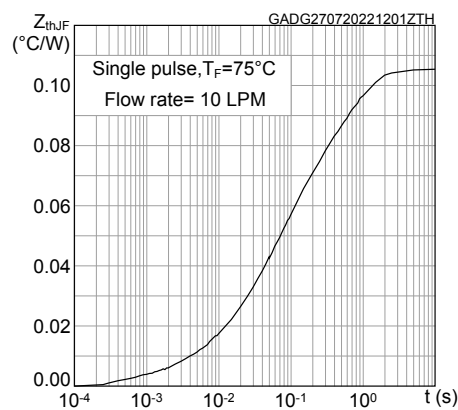


Figure 16. Typical thermal resistance vs flow rate

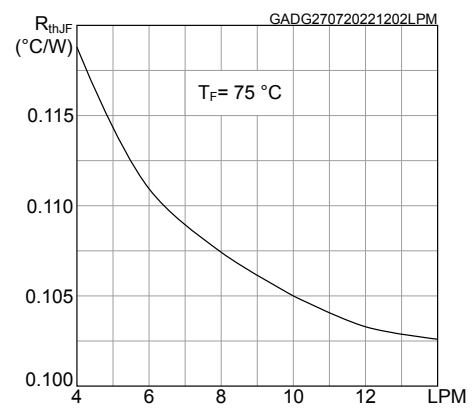
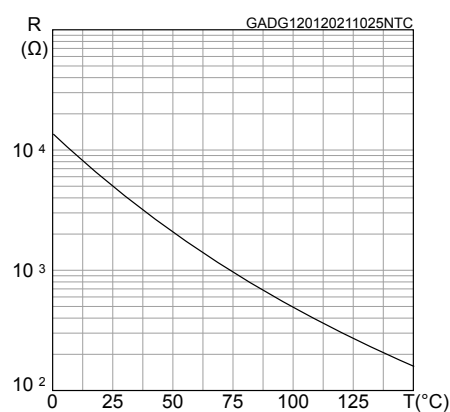


Figure 17. Typical NTC resistance vs temperature

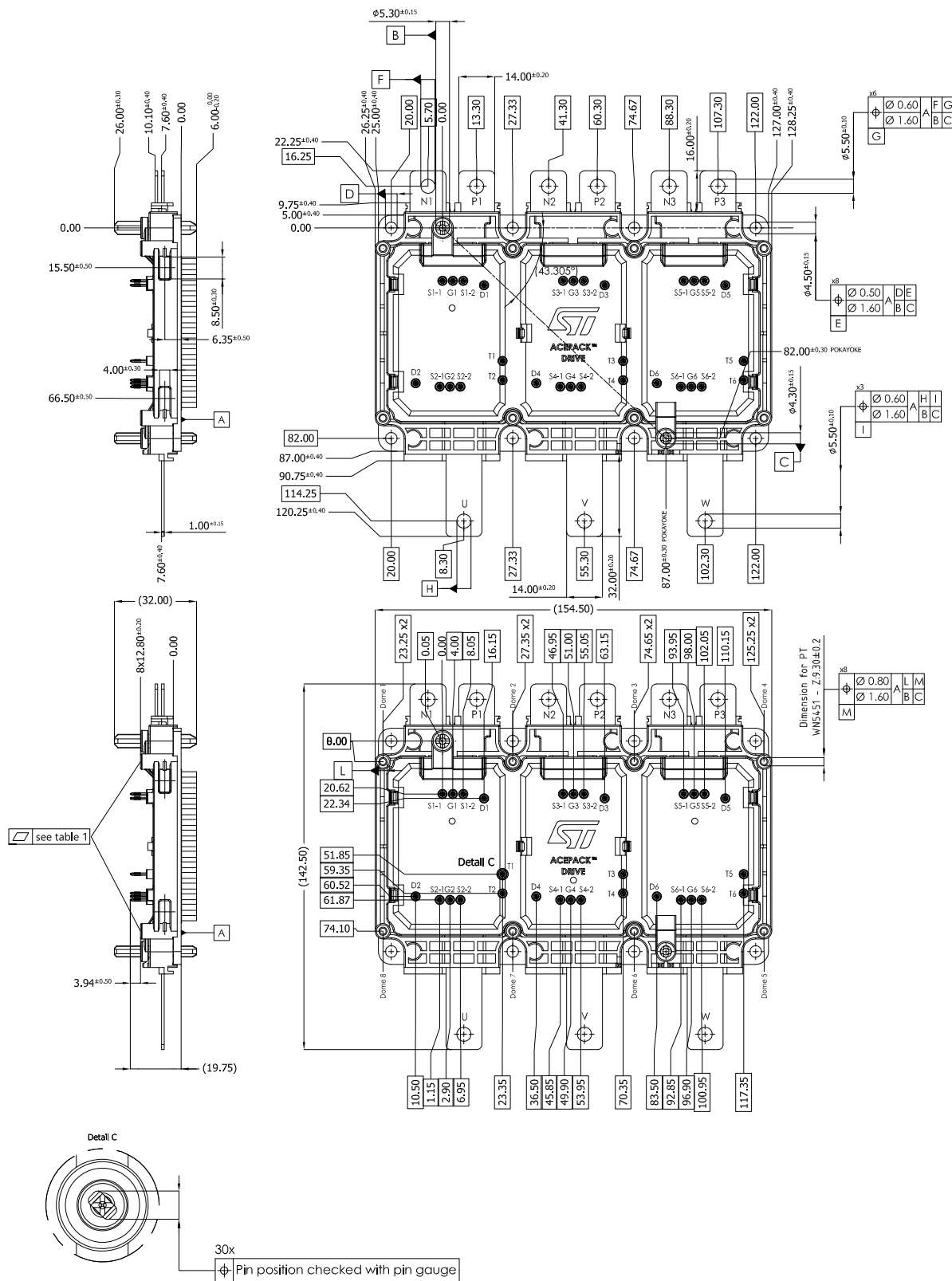


7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

7.1 ACEPACK DRIVE package information

Figure 20. ACEPACK DRIVE long tab package outline (dimensions are in mm.)



DM00518615_Long_REV5

Revision history

Table 8. Document revision history

Date	Revision	Changes
14-Sep-2021	1	First release.
08-May-2023	2	Modified Section Features . Modified the entire Section 1 Electrical ratings . Added Section 5 Electrical characteristics (curves) . Minor text changes.

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